

2SK2869(L), 2SK2869(S)

Silicon N Channel MOS FET
High Speed Power Switching

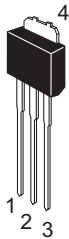
REJ03G1037-0200
(Previous: ADE-208-570)
Rev.2.00
Sep 07, 2005

Features

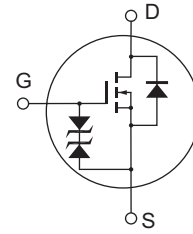
- Low on-resistance
 $R_{DS} = 0.033 \Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

RENESAS Package code: PRSS0004ZD-B
(Package name: DPAK(L)-(2))



RENESAS Package code: PRSS0004ZD-C
(Package name: DPAK(S))



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	20	A
Drain peak current	$I_{D(pulse)}^{*1}$	80	A
Body to drain diode reverse drain current	I_{DR}	20	A
Avalanche current	I_{AP}^{*3}	20	A
Avalanche energy	E_{AR}^{*3}	34	mJ
Channel dissipation	P_{ch}^{*2}	30	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

- Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

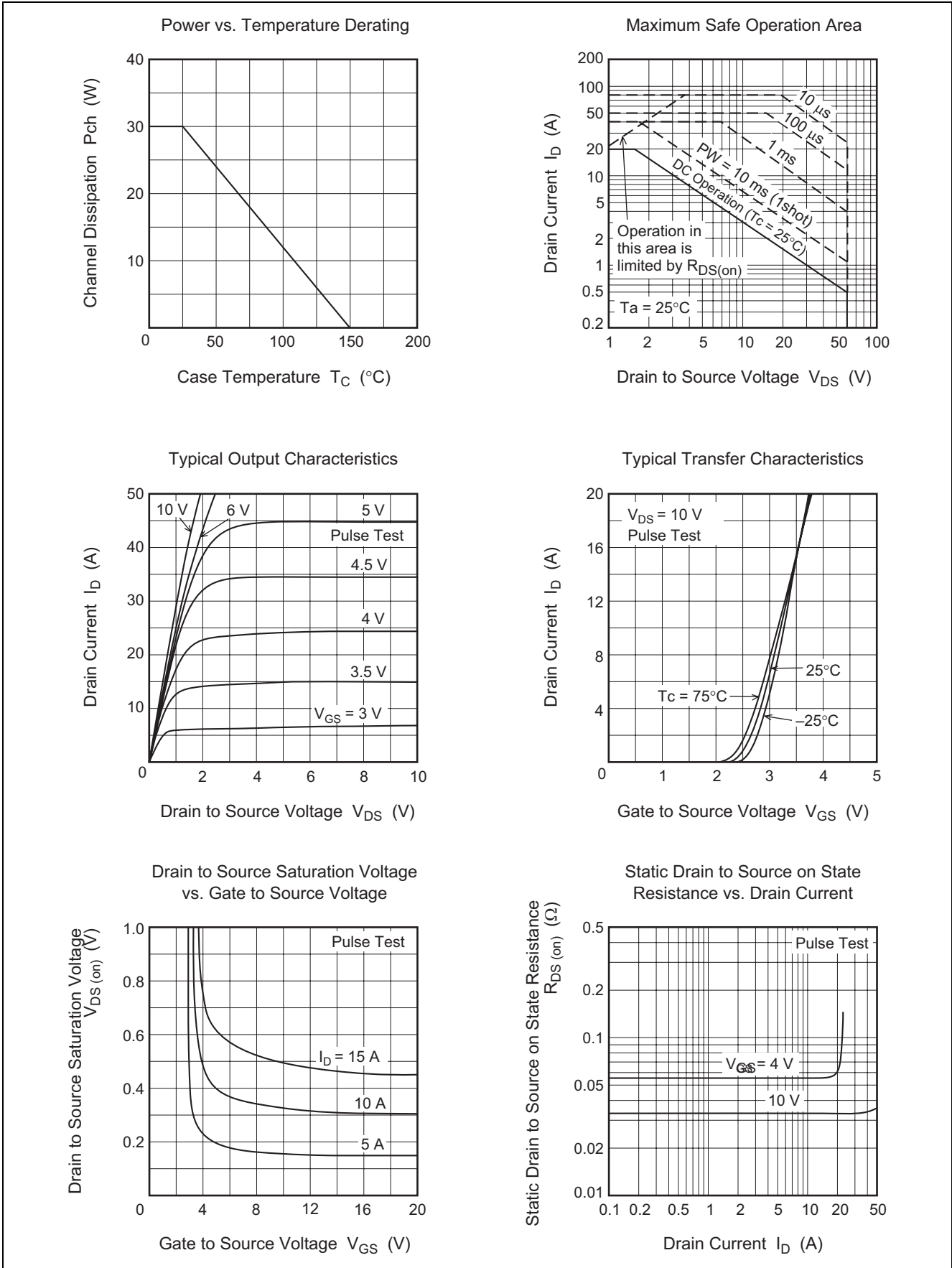
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.033	0.045	Ω	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}^{*4}$
	$R_{DS(on)}$	—	0.055	0.07	Ω	$I_D = 10 \text{ A}$, $V_{GS} = 4 \text{ V}^{*4}$
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = 10 \text{ A}$, $V_{DS} = 10 \text{ V}^{*4}$
Input capacitance	C_{iss}	—	740	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	380	—	pF	
Reverse transfer capacitance	C_{rss}	—	140	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	
Rise time	t_r	—	110	—	ns	$I_D = 10 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 3 \Omega$
Turn-off delay time	$t_{d(off)}$	—	105	—	ns	
Fall time	t_f	—	120	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 20 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	40	—	V	$I_F = 20 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu s$

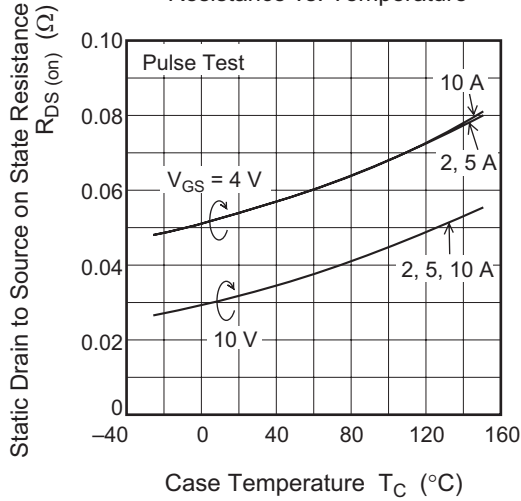
- Note: 4. Pulse test

Main Characteristic

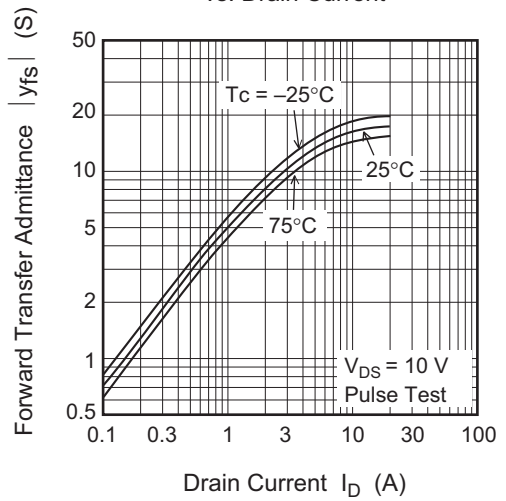


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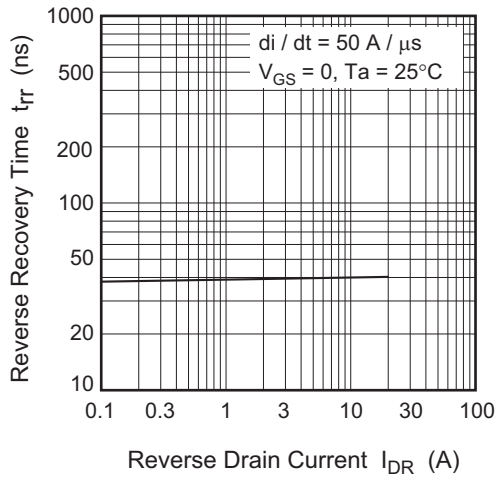
Static Drain to Source on State Resistance vs. Temperature



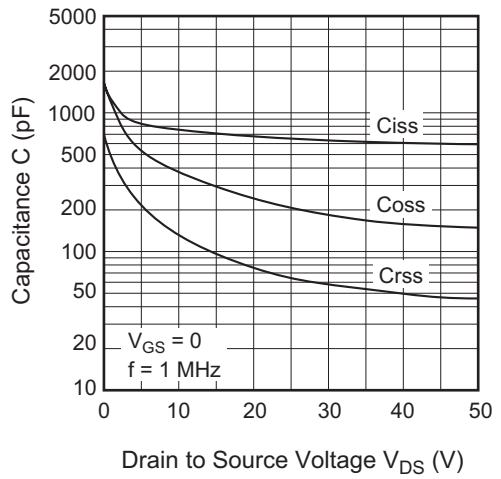
Forward Transfer Admittance vs. Drain Current



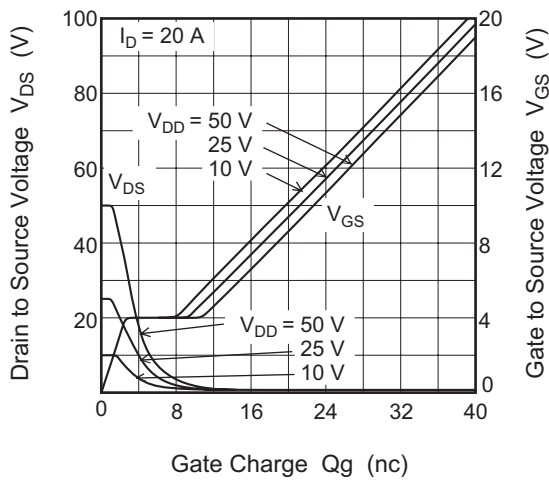
Body to Drain Diode Reverse Recovery Time



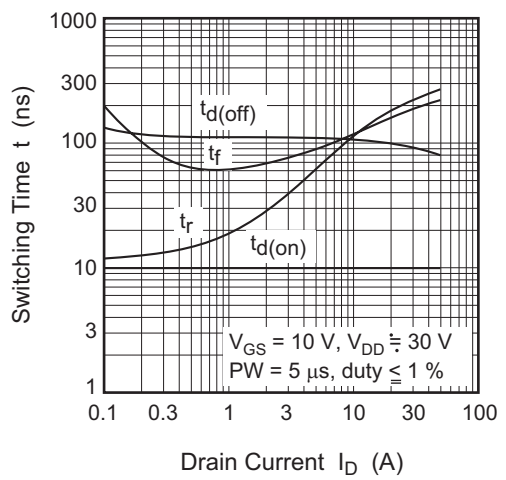
Typical Capacitance vs. Drain to Source Voltage



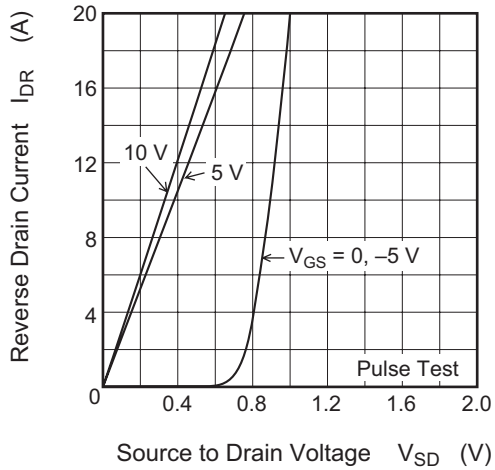
Dynamic Input Characteristics



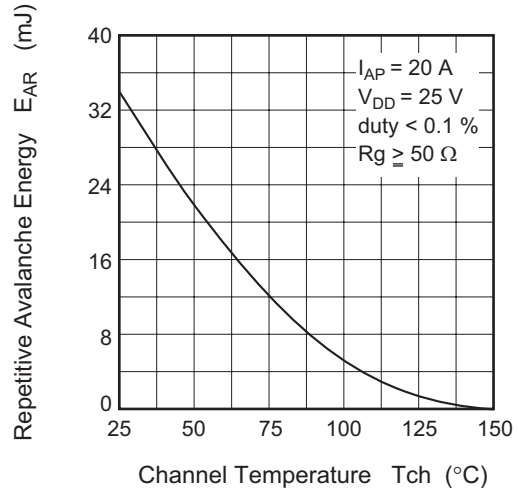
Switching Characteristics



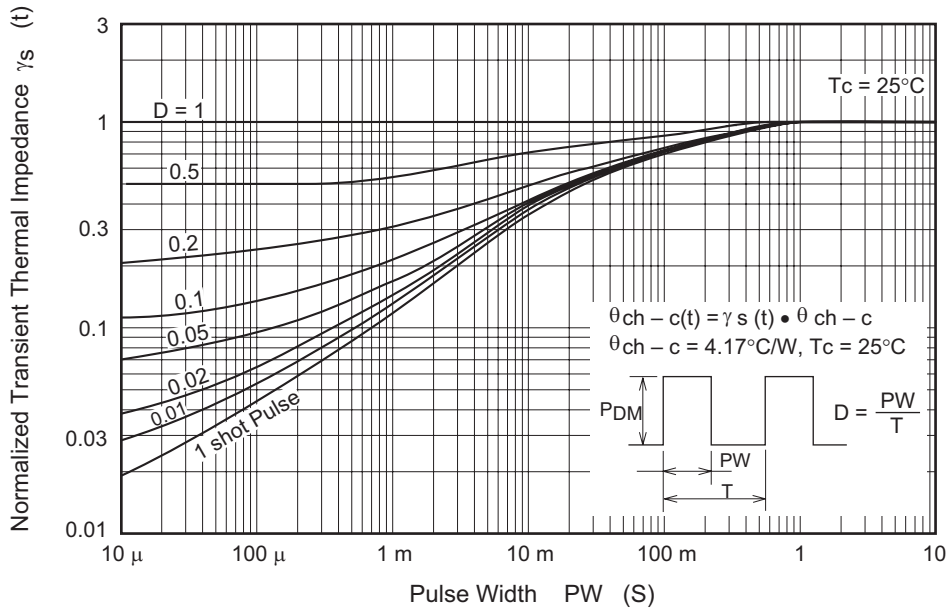
Reverse Drain Current vs. Source to Drain Voltage



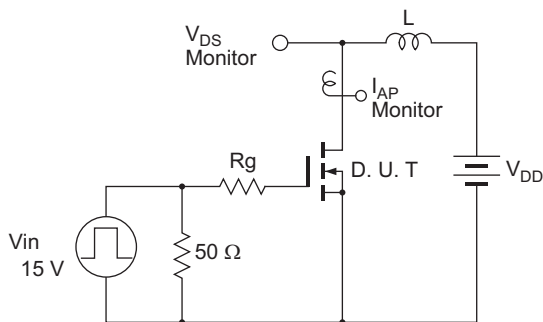
Maximum Avalanche Energy vs. Channel Temperature Derating



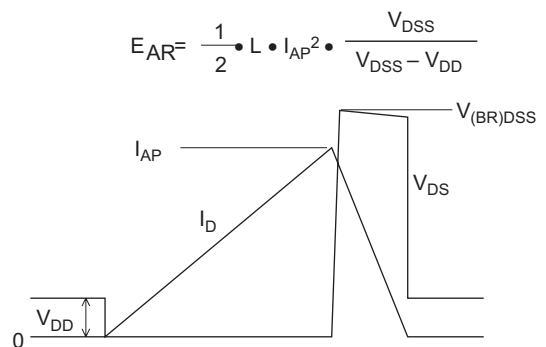
Normalized Transient Thermal Impedance vs. Pulse Width



Avalanche Test Circuit

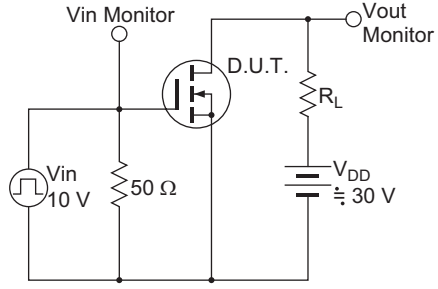


Avalanche Waveform

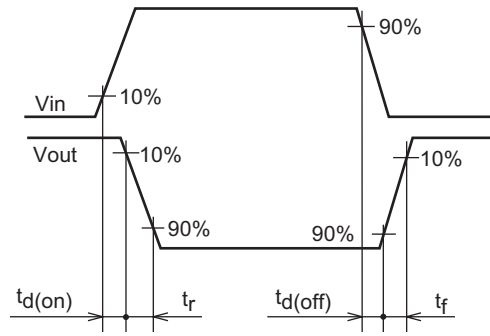


$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

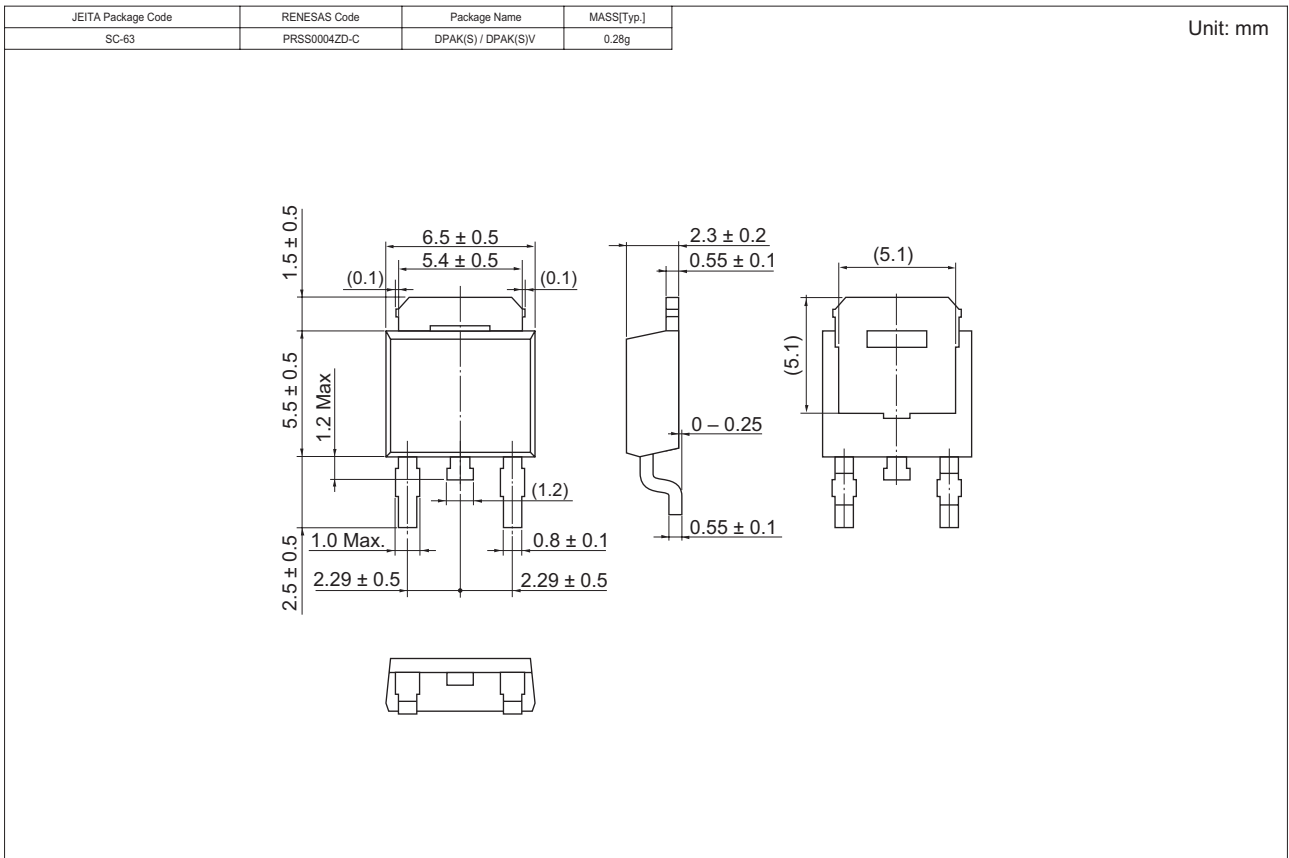
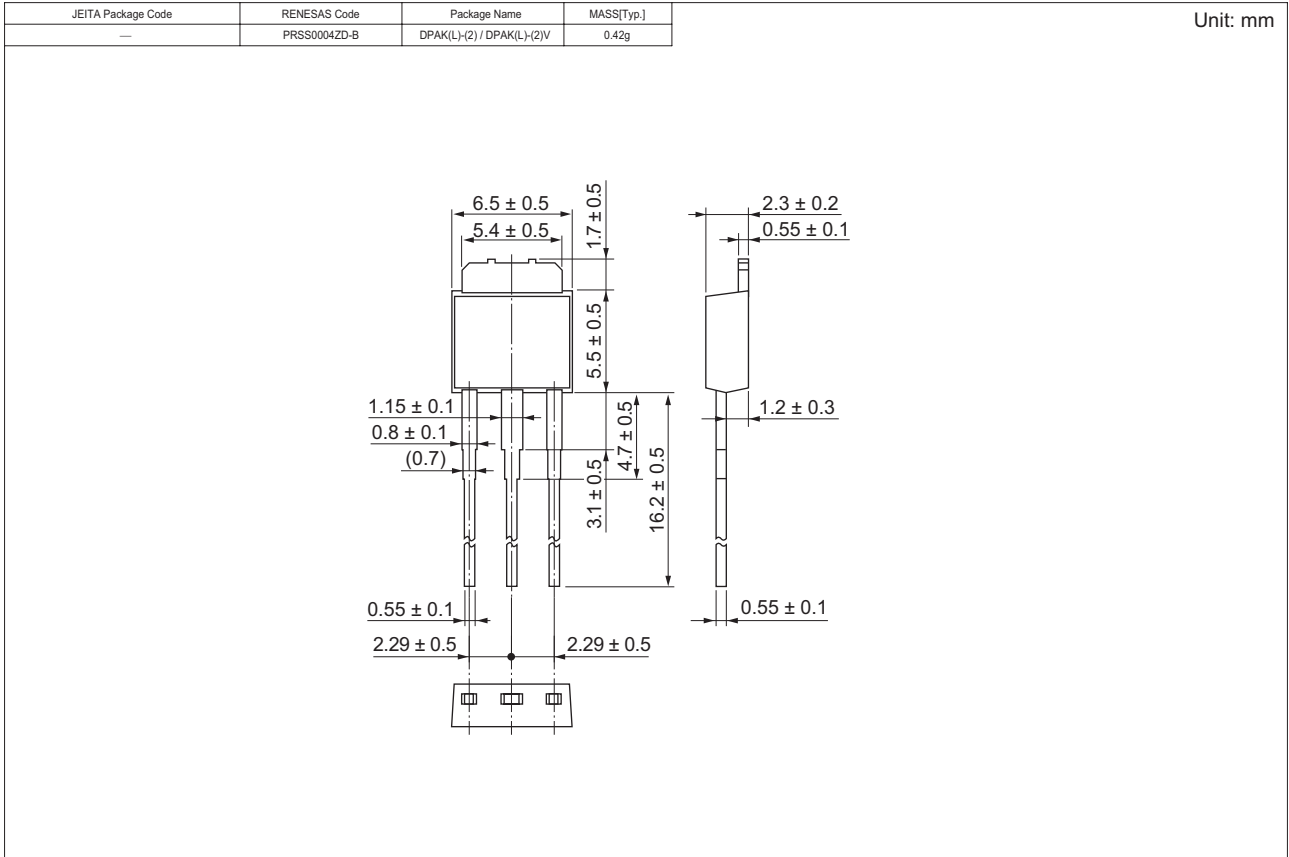
Switching Time Test Circuit



Switching Time Waveforms



Package Dimensions



Ordering Information
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Part Name	Quantity	Shipping Container
2SK2869L-E	3200 pcs	Box (Sack)
2SK2869STL-E	3000 pcs	Taping

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